TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

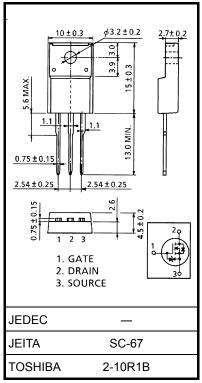
2SK3754

Relay Drive, DC–DC Converter and Motor Drive Applications

- 4.5-V gate drive
- Low drain-source ON resistance: R_{DS} (ON) = 71 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 5.0 \text{ S} (typ.)$
- Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- Enhancement-model: $V_{th} = 1.3 \sim 2.5 \text{ V} (V_{DS} = 10 \text{ V}, \text{I}_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage	•	V _{DSS}	30	V
Drain-gate voltage (F	R _{GS} = 20 kΩ)	V _{DGR}	30	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	DC (Note 1)	I _D	5	А
	Pulse (Note 1)	I _{DP}	15	A
Drain power dissipat	ion (Tc = 25°C)	PD	25	W
Single pulse avalance	he energy (Note 2)	E _{AS}	4.0	mJ
Avalanche current		I _{AR}	2.5	А
Repetitive avalanche	e energy (Note 3)	E _{AR}	2.5	mJ
Channel temperature	e	T _{ch}	150	°C
Storage temperature	range	T _{stg}	-55~150	°C



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	5.0	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2: V_{DD} =24 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 25 Ω , I_{AR} = 2.5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

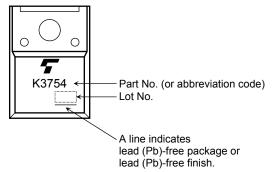
Electrical Characteristics (Ta = 25°C)

Charae	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage curre	ent	I _{GSS}	$V_{GS} = \pm 16$ V, $V_{DS} = 0$ V	_		±10	μA	
Drain cut-off curre	nt	I _{DSS}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	10	μA	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30			v	
		V (BR) DSX	$I_{\rm D} = 10 \text{ mA}, V_{\rm GS} = -20 \text{ V}$			_	v	
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	1.3		2.5	V	
Drain-source ON resistance		Page (only	$V_{GS} = 4.5 \text{ V}, \text{ I}_D = 2.5 \text{ A}$		78	99	mΩ	
		R _{DS (ON)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$		71	89		
Forward transfer admittance		Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$	2.5	5.0		S	
Input capacitance		C _{iss}			1250	_	pF	
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, \text{f} = 1 \text{MHz}$		155	_		
Output capacitance		C _{oss}		_	170	_		
Switching time	Rise time	tr	$V_{GS}^{10 V}$ 0 V C_{GS}^{C} V_{GS}^{C} V_{C	_	7	_	- ns	
	Turn-on time	t _{on}			16			
	Fall time	t _f			18			
	Turn-off time	t _{off}	Duty ≦ 1%, t _w = 10 μs	_	69			
Total gate charge		Qg		_	25			
Gate-source charge		Q _{gs}	$V_{DD}\simeq 24$ V, $V_{GS}=10$ V, $I_{D}=5$ A	_	20		nC	
Gate-drain charge		Q _{gd}			5			

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	5	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	15	А
Reverse recovery time	t _{rr}	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V},$	_	37	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 50 A/µs		20		nC

Marking



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20070701-EN

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